

DFN 2×2B-6L P MOS

P-Channel Enhancement Mode Field Effect Transistor in a DFN 2×2B-6L Plastic Package.

$V_{DS} (V) = -20V$ $I_D = -12A$

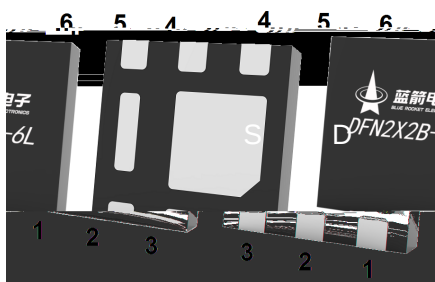
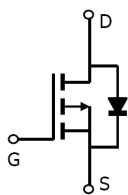
$R_{DS(ON)}@-4.5V \leq 17m\Omega$ (Type.14.5m Ω)

$R_{DS(ON)}@-2.5V \leq 25m\Omega$ (Type.18m Ω)

$R_{DS(ON)}@-1.8V \leq 38m\Omega$ (Type.24.5m Ω)

HF Product.

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

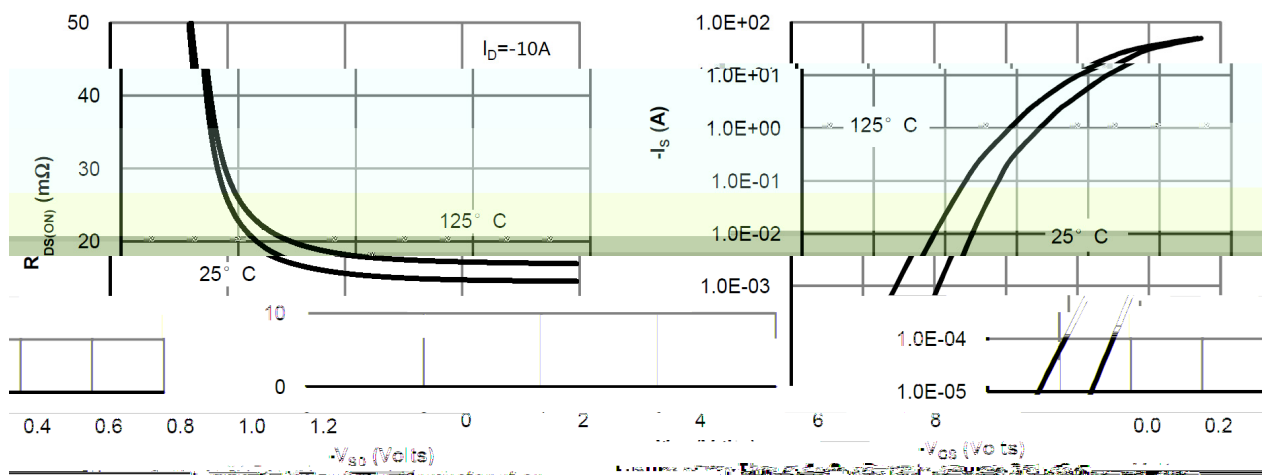
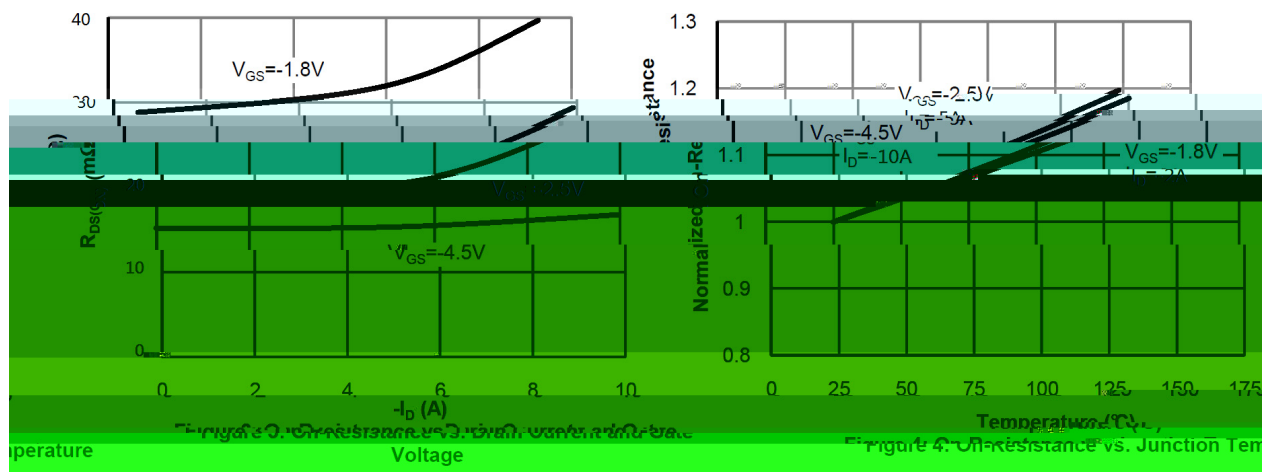
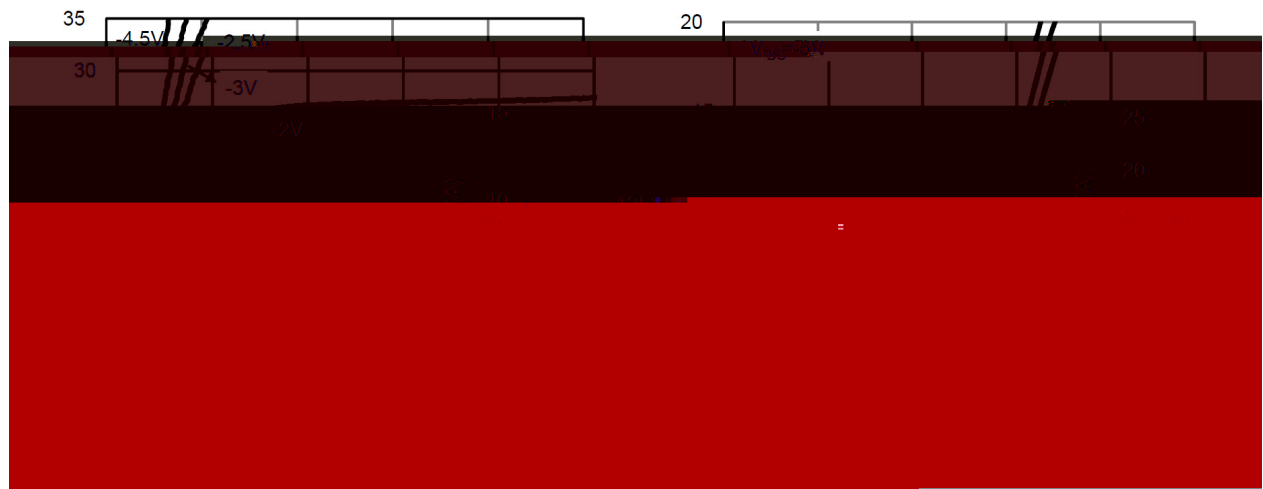


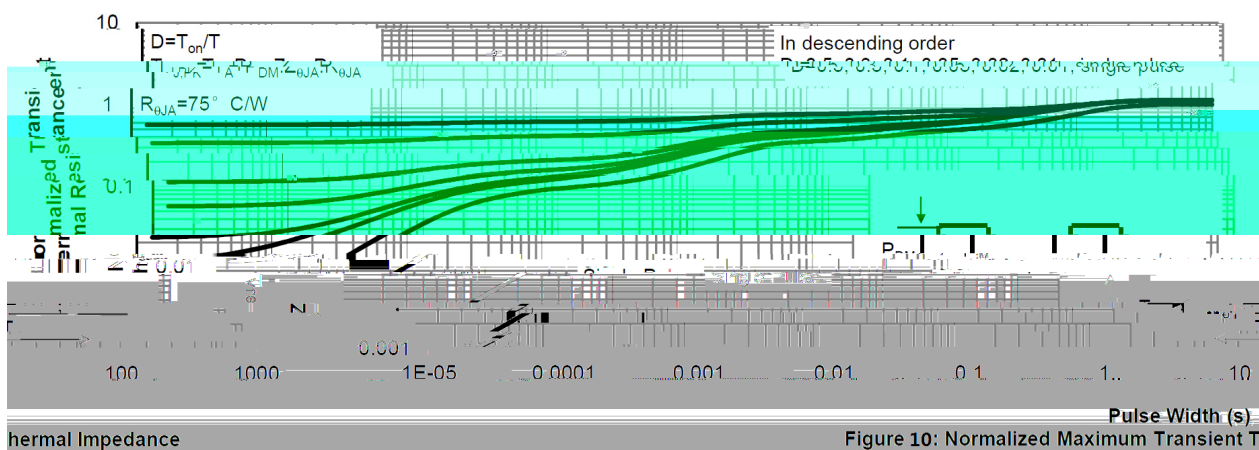
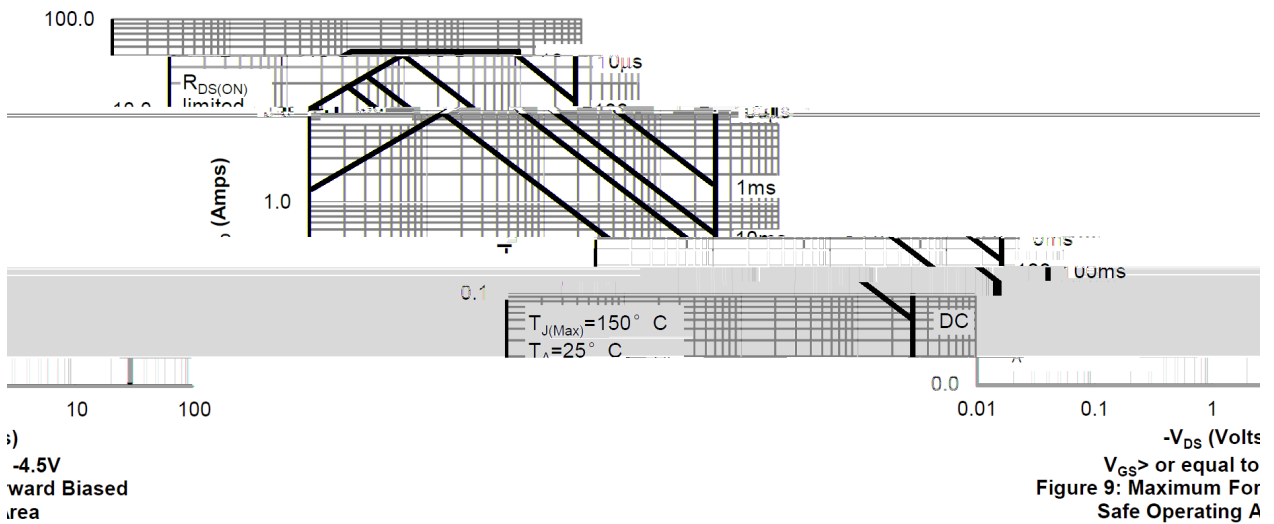
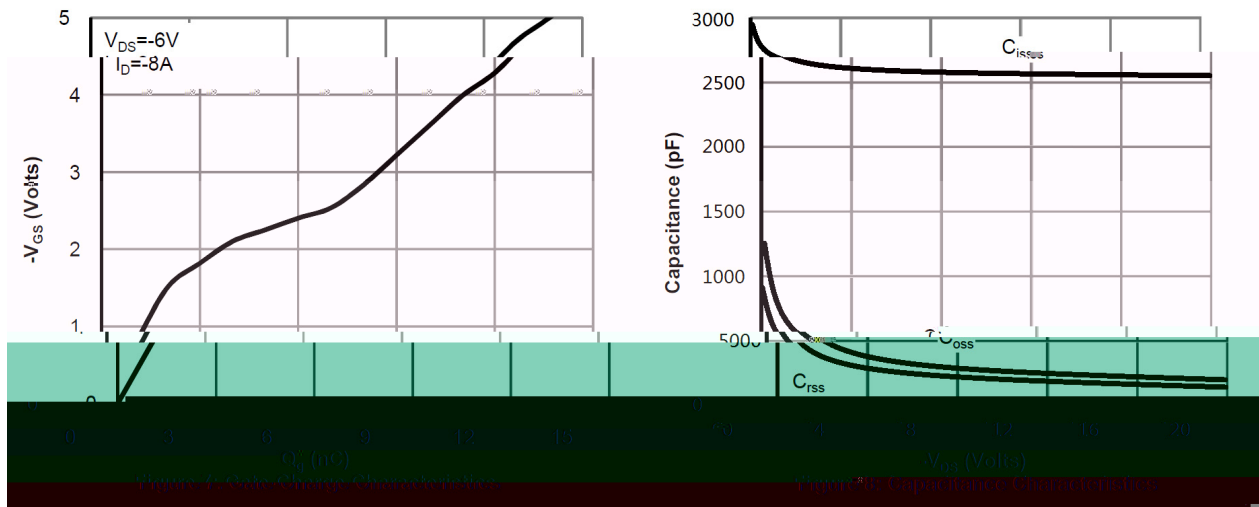
出脚	定义
Pin1	D
Pin2	D
Pin3	G
Pin4	S
Pin5	D
Pin6	D

See Marking Instructions.

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	± 12	V
Continuous Drain Current		$I_D (T_a=25^{\circ}\text{C})$	-12	A
Pulsed Drain Current		I_{DM}	-44	A
Avalanche Current		I_{AS}	-13	A
Avalanche energy $L=0.5\text{mH}$		E_{AS}	59	mJ
Power Dissipation for Single Operation		$P_D (T_a=25^{\circ}\text{C})$	3.0	W
Maximum Junction Temperature		T_J	150	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 150	$^{\circ}\text{C}$
Thermal Resistance-Junction to Ambient	t 10s	$R_{\theta JA}$	40	$^{\circ}\text{C/W}$
	Steady State		75	$^{\circ}\text{C/W}$

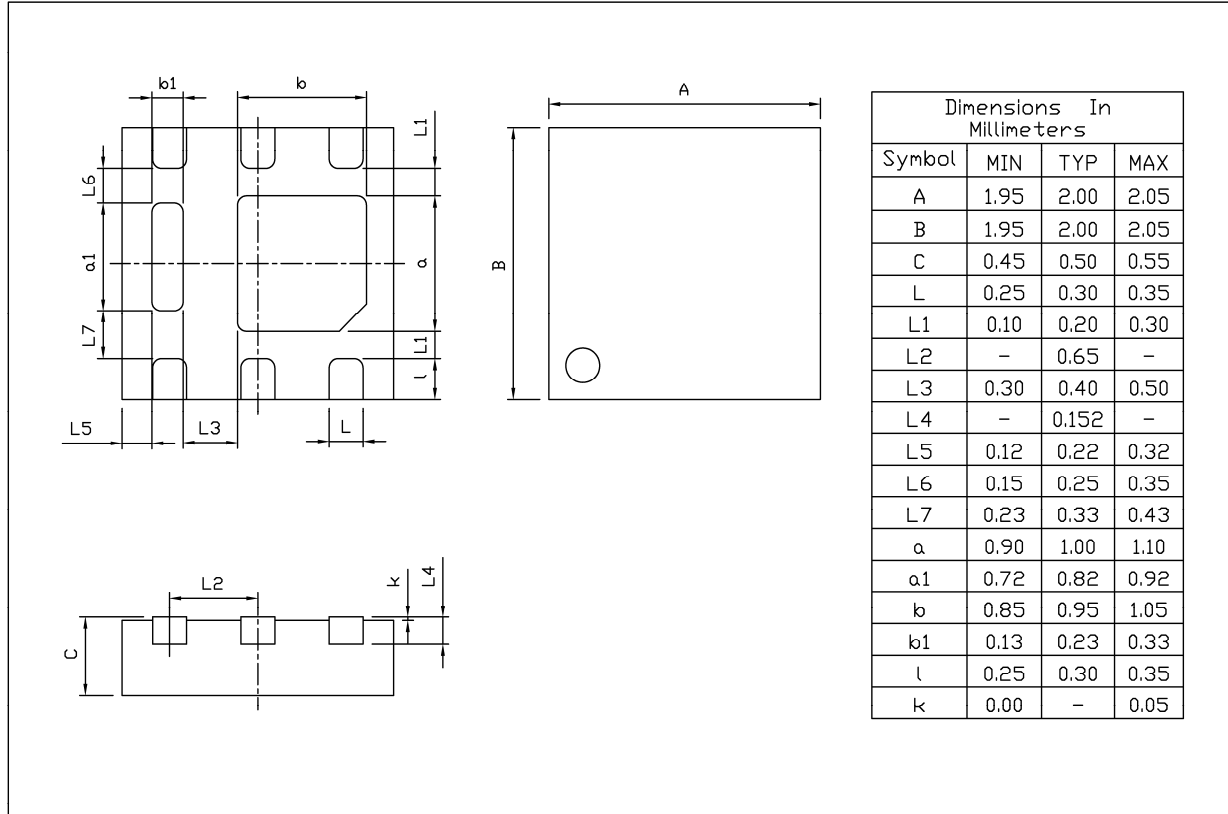
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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DFN2 X2B-6L-0.5

Unit:mm



Rev.01 202006



BR

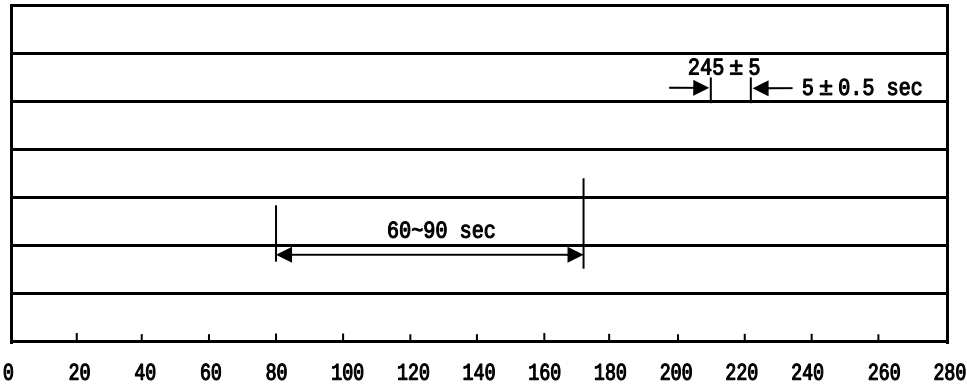
150P02

Note:

BR: Company Code

150P02: Product Type Code

*****: Lot No. Code, code change with Lot No



- Note:
- 1

150 180

60 90sec;

2

245±5

5±0.5sec;

3

2 10 /sec.
- 1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5℃

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
DFN2×2B-6L	4,000	10	40,000	4	160,000	7 ×8	210×205×205	445×435×230